IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A hot plate for heating a wafer comprising a ceramic substrate, said ceramic substrate having a lower face having a surface roughness of 2 μm or less and an upper face,

wherein a resistance element pattern having a thickness dispersion of ±3 μm or less is formed on the lower face of the ceramic substrate; and

wherein said resistance element comprises a first layer comprising titanium; a second layer comprising molybdenum and having a larger thickness than said first layer, on said first layer; and a third layer comprising nickel and having an intermediate thickness between the thickness of said first layer and that of said second layer, on said second layer.

Claim 2 (Original): The hot plate according to claim 1, wherein the thickness dispersion of the resistance element is ±1 μm or less.

Claim 3 (Previously Presented): The hot plate according to claim 1, wherein the thickness of said resistance element is from 0.5 to 500 μm.

Claim 4 (Previously Presented): The hot plate according to claim 1, wherein the thickness of said resistance element is from 1 to 10 μm.

Claim 5 (Previously Presented): The hot plate according to claim 1, wherein said ceramic substrate is at least one kind selected from a nitride ceramic and a carbide ceramic.

Claims 6-8 (Canceled).

Claim 9 (Currently Amended): The hot plate according to claim 1, wherein ~~said resistance element comprises a~~ said titanium layer ~~having~~ has a thickness of 0.1 to 0.5 μm, ~~a~~ said molybdenum layer ~~having~~ has a thickness of 0.5 to 7.0 μm, on said titanium layer, and ~~a~~ said nickel layer ~~having~~ has a thickness of 0.4 to 2.5 μm, on said molybdenum layer.

Claims 10-27 (Canceled).

Claim 28 (Previously Presented): A process comprising heating a wafer with the hot plate according to claim 1.

Claim 29 (Previously Presented): A hot plate for heating a wafer comprising a ceramic substrate, said ceramic substrate having a lower face having a surface roughness of 2 μm or less and an upper face,

wherein

a resistance element pattern having a thickness dispersion of ±3 μm or less is formed on the lower face of the ceramic substrate,

the thickness dispersion being the larger of the absolute value of Tmax – Tav and the absolute value of Tmin – Tav, Tav being an average thickness obtained by averaging thicknesses of arbitrarily selected 10 points of the resistance element, Tav being within a range of 3 to 500 μm, Tmax being the maximum thickness of said 10 points, and Tmin being the minimum thickness of said 10 points.

Claim 30 (Previously Presented): The hot plate according to claim 29, wherein the thickness dispersion of the resistance element is ±1 μm or less.

Claim 31 (Previously Presented): The hot plate according to claim 29, wherein the thickness of said resistance element is from 0.5 to 500 μm.

Claim 32 (Previously Presented): The hot plate according to claim 29, wherein the thickness of said resistance element is from 1 to 10 μm.

Claim 33 (Previously Presented): The hot plate according to claim 29, wherein said ceramic substrate is at least one kind selected from a nitride ceramic and a carbide ceramic.

Claim 34 (Previously Presented): The hot plate according to claim 29, wherein said resistance element has a multilayer structure, and among a plurality of layers constituting said resistance element, the layer nearest to the substrate comprises titanium or chromium.

Claim 35 (Previously Presented): The hot plate according to claim 29, wherein said resistance element comprises a first layer comprising titanium; a second layer comprising molybdenum and having a larger thickness than said first layer, on said first layer; and a third layer comprising nickel and having an intermediate thickness between the thickness of said first layer and that of said second layer, on said second layer.

Claim 36 (Previously Presented): The hot plate according to claim 29,

wherein said resistance element comprises a titanium layer having a thickness of 0.1 to 0.5 μm, a molybdenum layer having a thickness of 0.5 to 7.0 μm, on said titanium layer, and a nickel layer having a thickness of 0.4 to 2.5 μm, on said molybdenum layer.

Claim 37 (Previously Presented): The hot plate according to claim 29,

wherein said resistance element pattern is formed by a dry process.

Claim 38 (Previously Presented): The hot plate according to claim 37,

wherein the thickness dispersion of the resistance element is ± 1 μm or less.

Claim 39 (Previously Presented): The hot plate according to claim 37,

wherein the thickness of said resistance element is from 0.5 to 500 μm.

Claim 40 (Previously Presented): The hot plate according to claim 37,

wherein the thickness of said resistance element is from 1 to 10 μm.

Claim 41 (Previously Presented): The hot plate according to claim 37,

wherein said ceramic substrate is at least one kind selected from a nitride ceramic and a carbide ceramic.

Claim 42 (Previously Presented): The hot plate according to claim 37,

wherein said dry process is RF sputtering.

Claim 43 (Previously Presented): The hot plate according to claim 29, wherein said resistance element pattern is made of scaly noble metal powder.

Claim 44 (Previously Presented): The hot plate according to claim 43, wherein the thickness dispersion of the resistance element is ± 1 μm or less.

Claim 45 (Previously Presented): The hot plate according to claim 43, wherein the thickness of said resistance element is from 0.5 to 500 μm.

Claim 46 (Previously Presented): The hot plate according to claim 43, wherein the thickness of said resistance element is from 3 to 10 μm.

Claim 47 (Previously Presented): The hot plate according to claim 43, wherein said ceramic substrate is at least one kind selected from a nitride ceramic and a carbide ceramic.

Claim 48 (Previously Presented): A process comprising heating a wafer with the hot plate according to claim 29.

Claim 49 (New): A process for producing the hot plate as claimed in claim 29, which comprises:

forming said resistance element by a film-depositing method based on a dry process.

Claim 50 (New): A process for producing the hot plate as claimed in claim 29, which comprises:

forming said resistance element by RF sputtering.

Claim 51 (New): A process for producing the hot plate as claimed in claim 29, which comprises:

printing a resistance element paste made of scaly noble metal powder and firing the paste.